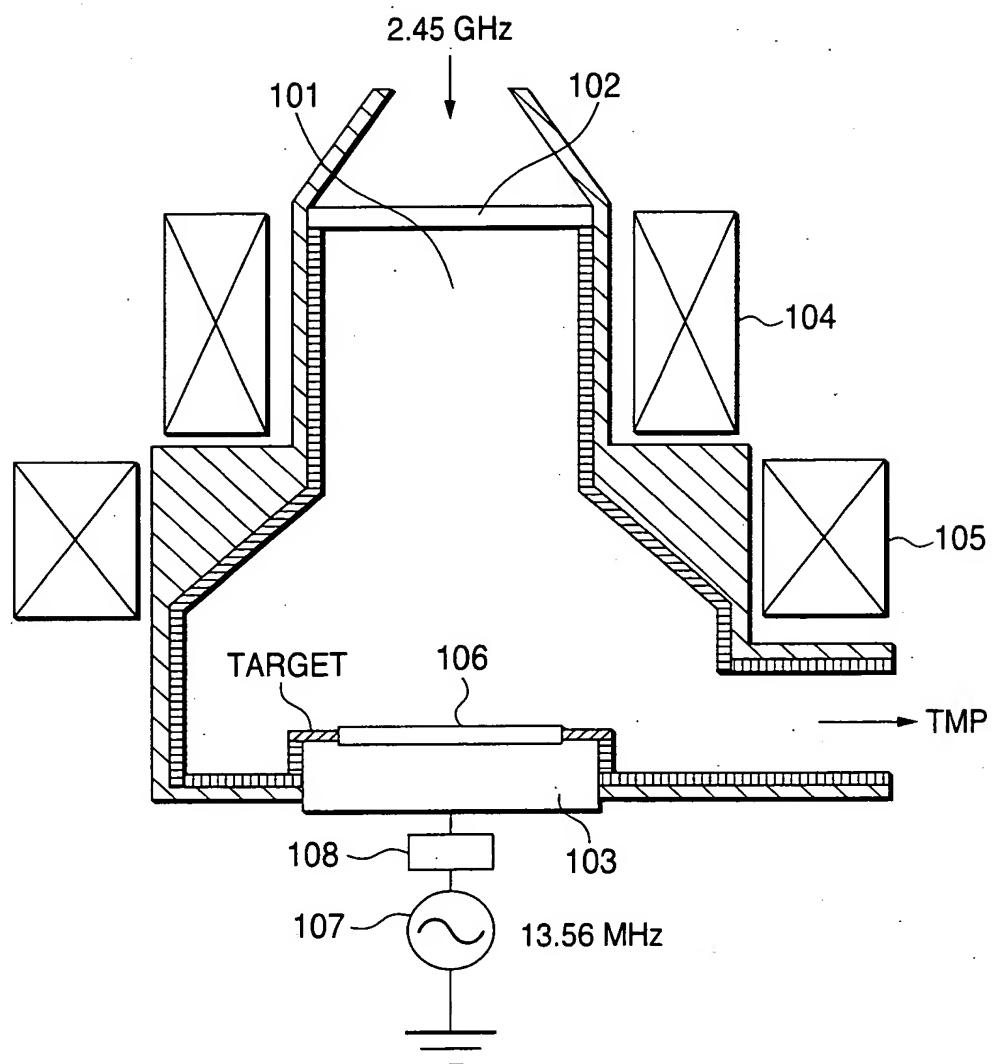


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FIG. 1





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FIG. 2A

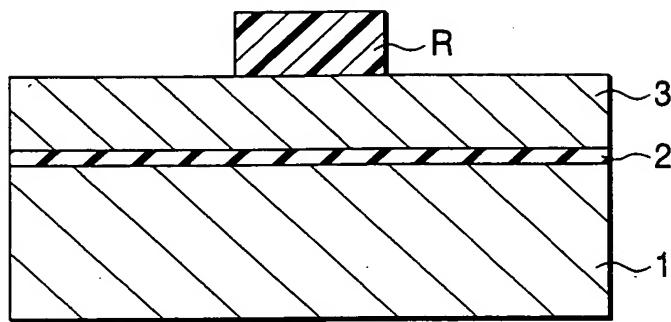


FIG. 2B

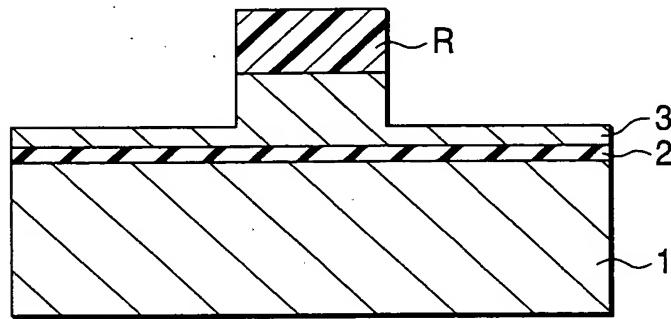
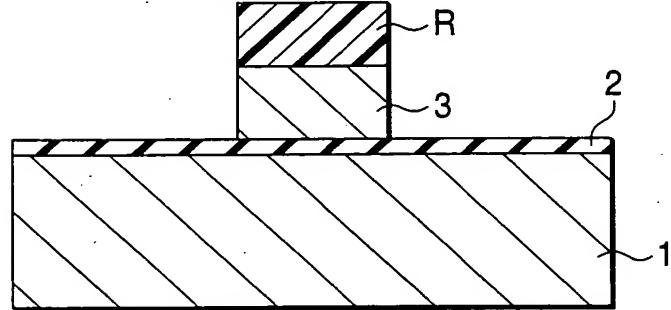


FIG. 2C



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FIG. 3

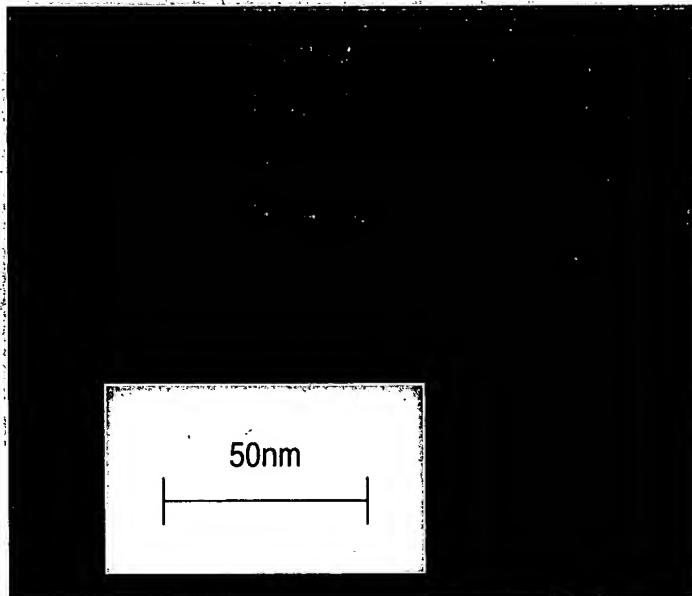
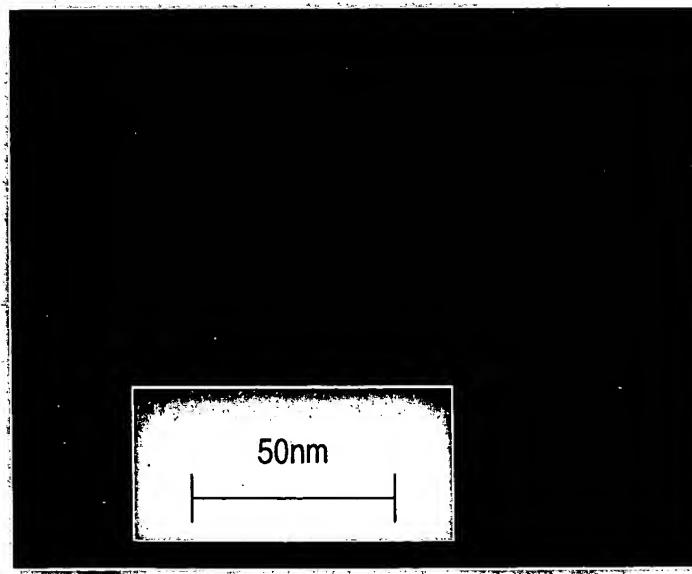


FIG. 4





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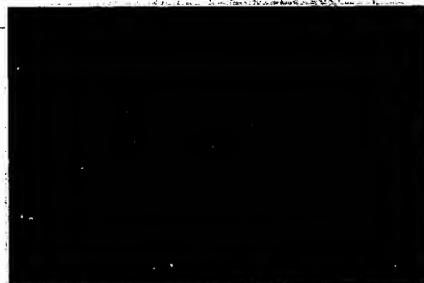
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FIG. 5

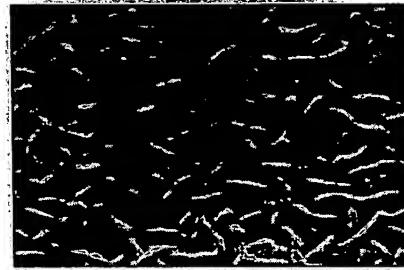


FIG. 6A



PARTIALLY ETCHED polySi

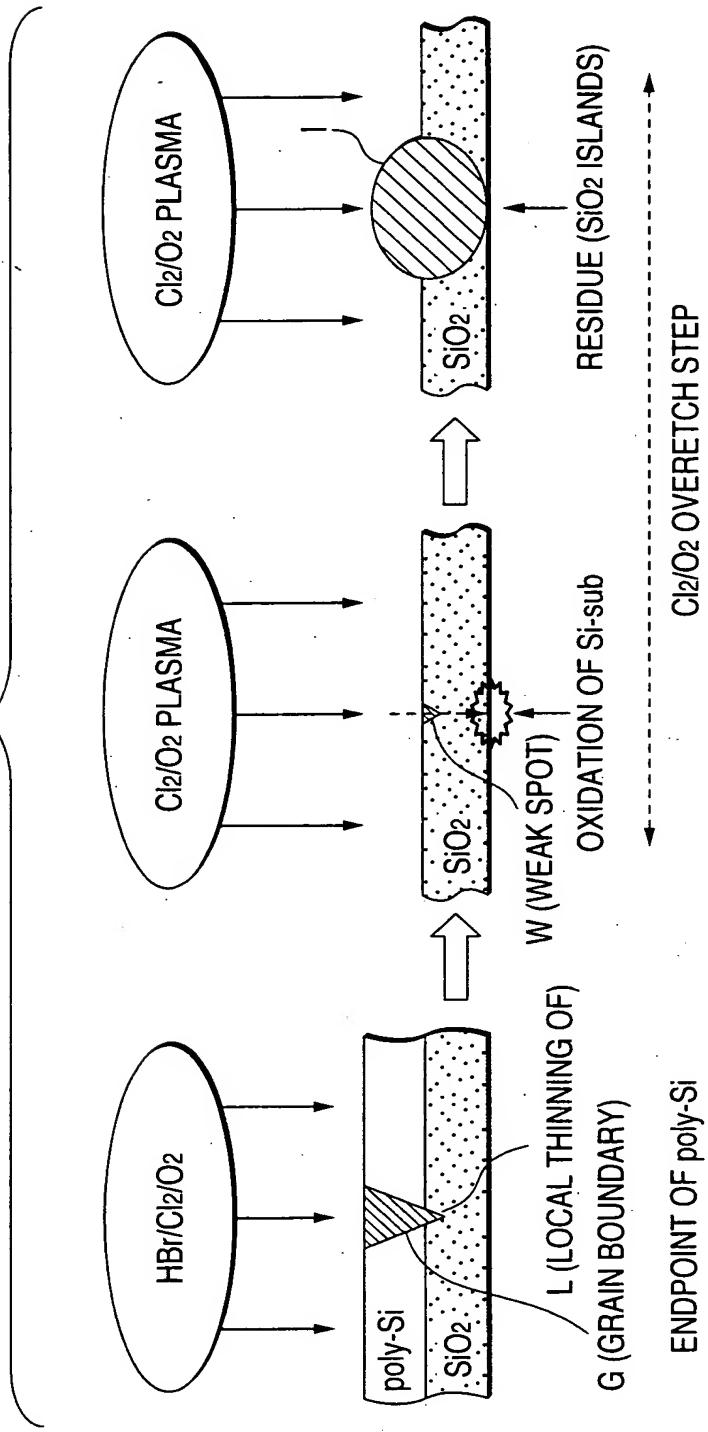
FIG. 6B



GATE OXIDE SURFACE
SURFACE MORPHOLOGY OF polySi AND GATE OXIDE



FIG. 7





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FIG. 8

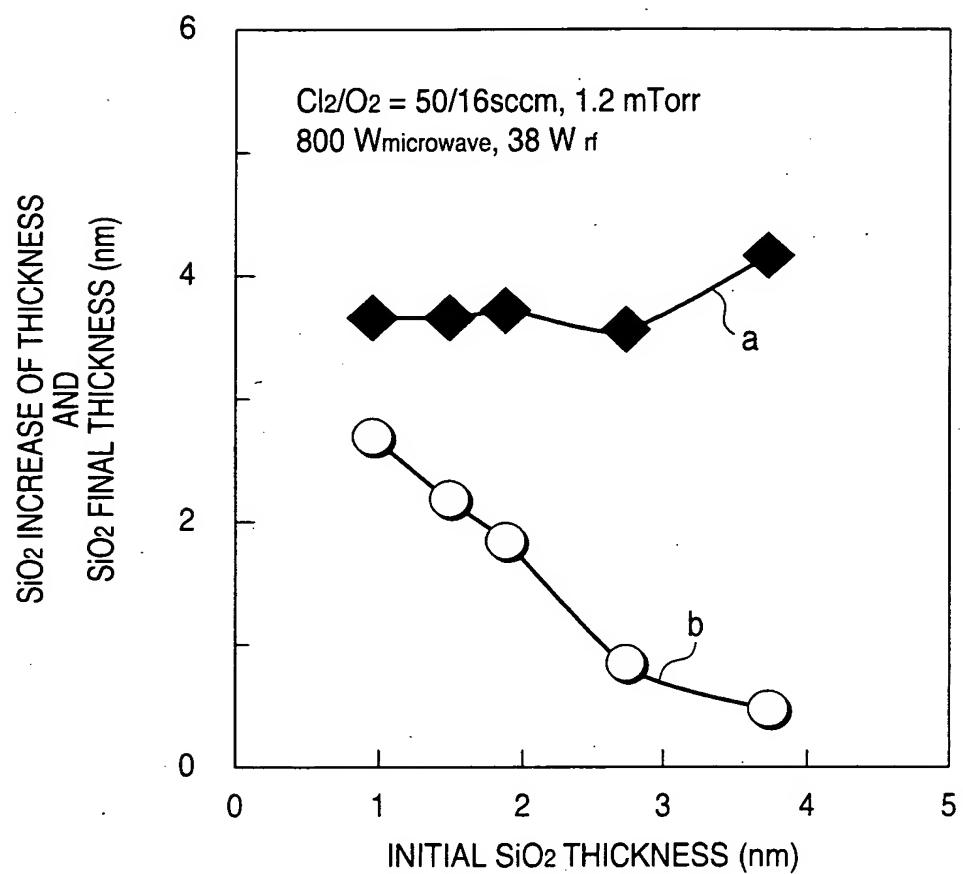




FIG. 9

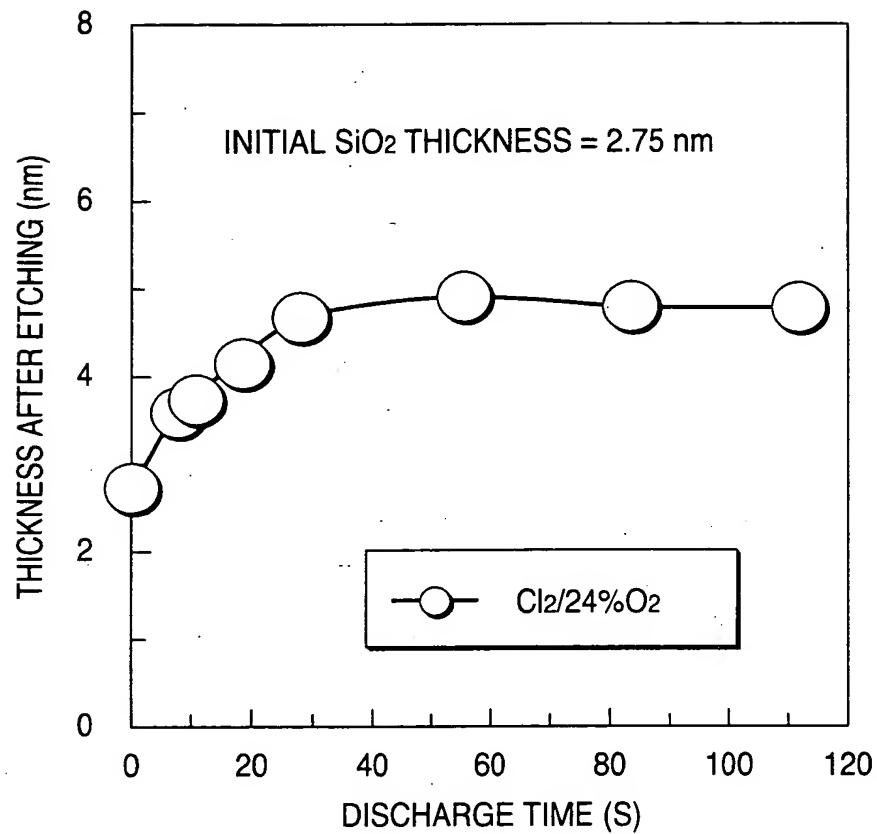


FIG. 10

